

ABSTRACT

The present application relates to a photoresist stripping method and system for a Chip-On-Wafer process. The photoresist stripping method for the Chip-On-Wafer process includes: wetting a wafer to be subjected to photoresist removal; controlling the rotation speed of the wafer to be within the range of 30RPM to 200RPM, and applying a first preset time of mega-sonic wave to the wetted wafer to remove the photoresist. The present application solves the problem in the prior art that splashing liquid is generated due to the excessively high rotation speed, and further causes the splashed liquid to adhere to the inner wall of the chamber and drip onto the wafer surface to affect the next process, ultimately leading to the low production yield, and improving the production yield.